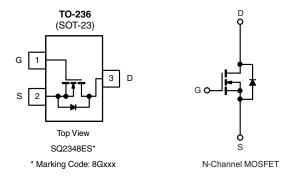


# Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.024			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.032			
I <sub>D</sub> (A)	8			
Configuration	Single			



### **FEATURES**

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified<sup>c</sup>
- 100 % Rq and UIS Tested
- Material categorization:
   For definitions of compliance please see www.freescale.net.cn





ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	SQ2348ES-T1-GE3

ABSOLUTE MAXIMUM RATING	<b>5</b> (1 <sub>C</sub> = 25 °C, unless	s otherwise noted	٦)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	30	V	
Gate-Source Voltage		V <sub>GS</sub> ± 20		v	
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	8		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	5.3		
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	3.8	Α	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	32		
Single Pulse Avalanche Current	1 0.1 ml l	I <sub>AS</sub>	15.5		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	12	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	D	3	W	
	T <sub>C</sub> = 125 °C	$P_D$	1		
Operating Junction and Storage Temperatur	e Range	T <sub>J</sub> , T <sub>stq</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient F	PCB Mount <sup>b</sup>	$R_{thJA}$	166	°C/W	
Junction-to-Foot (Drain)		$R_{thJF}$	50		

### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.



# SQ2348ES Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	1			I.	ı	·	<u> </u>	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30	-	-	· v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$		1.5	2.0	2.5		
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 30 V	=.	-	1		
	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 175 °C	-	-	150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A	=.	0.020	0.024	Ω	
	В	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A, T <sub>J</sub> = 125 °C	=.	-	0.036		
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A, T <sub>J</sub> = 175 °C	-	-	0.042		
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 8 A	=.	0.026	0.032		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 3 A		=.	10	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		N <sub>DS</sub> = 15 V, f = 1 MHz	-	430	540	pF	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V		-	100	125		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	40	50		
Total Gate Charge <sup>c</sup>	Qg		V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5.5 A	-	7.95	14.5	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V		=.	1.6	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		=.	1.3	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		8.65	17.3	27	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	4.5	7		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, \text{ R}_{L} = 3.4 \Omega$ $I_{D} \cong 4.4 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		=.	8	12	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	21	32		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	6	9		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	32	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 3.5 A, V <sub>GS</sub> = 0 V		-	0.8	1.2	V	

### Notes

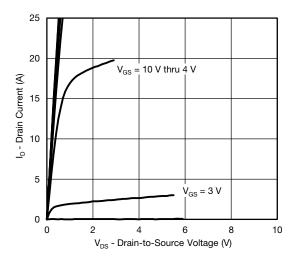
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

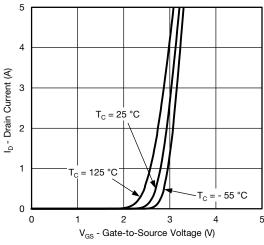


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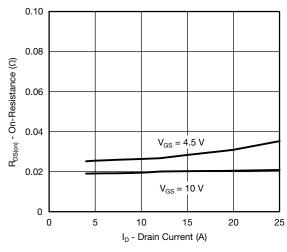
### **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



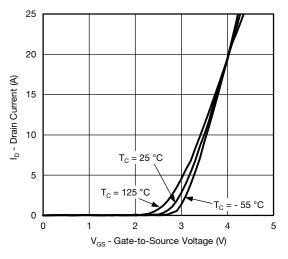
#### **Output Characteristics**



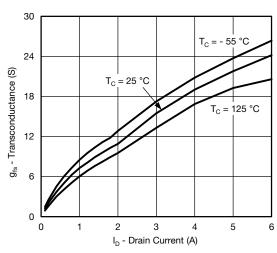
### **Transfer Characteristics**



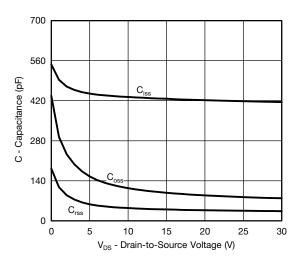
**On-Resistance vs. Drain Current** 



#### **Transfer Characteristics**



### Transconductance

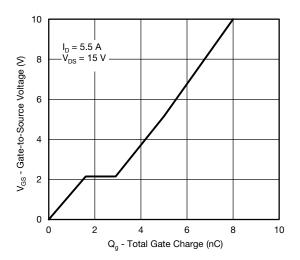


Capacitance

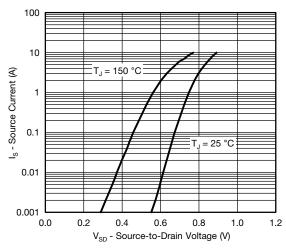


# Automotive N-Channel 30 V (D-S) 175 °C MOSFET

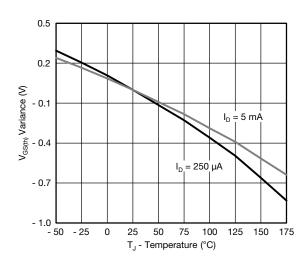
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \, ^{\circ}\text{C}$ , unless otherwise noted)



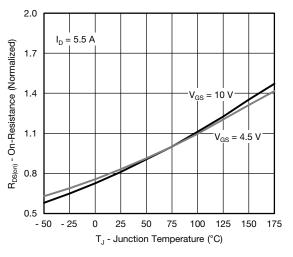
#### **Gate Charge**



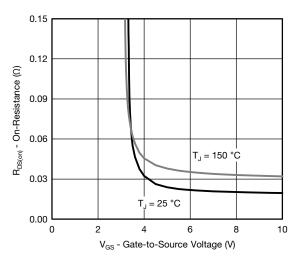
Source Drain Diode Forward Voltage



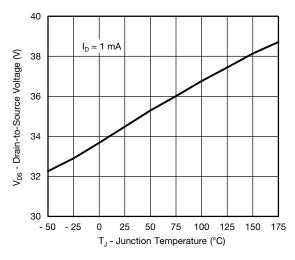
**Threshold Voltage** 



On-Resistance vs. Junction Temperature



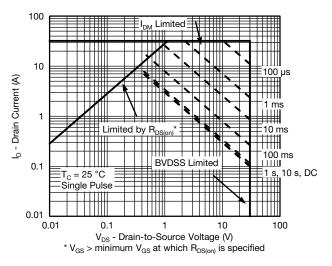
On-Resistance vs. Gate-to-Source Voltage



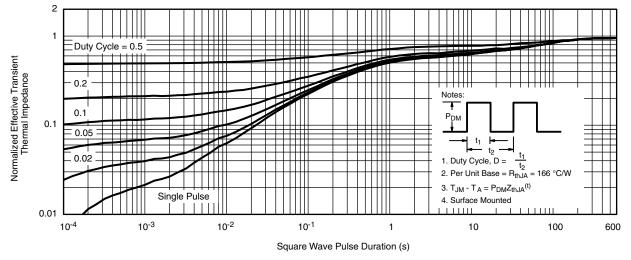
**Drain Source Breakdown vs. Junction Temperature** 

# Automotive N-Channel 30 V (D-S) 175 °C MOSFET

### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



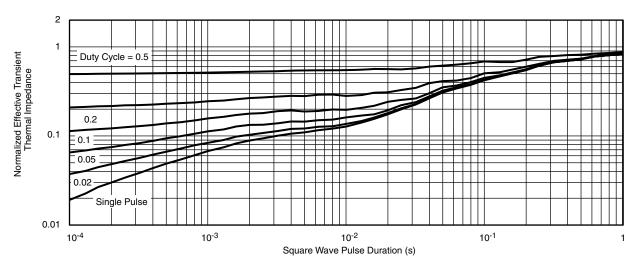
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

# Automotive N-Channel 30 V (D-S) 175 °C MOSFET

### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



# SQ2348ES Automotive N-Channel 30 V (D-S) 175 °C MOSFET

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